

# HVL142AM

## Silicon Epitaxial Planar Pin Diode for Antenna Switching

REJ03G0198-0200

Rev.2.00

Jan 19, 2006

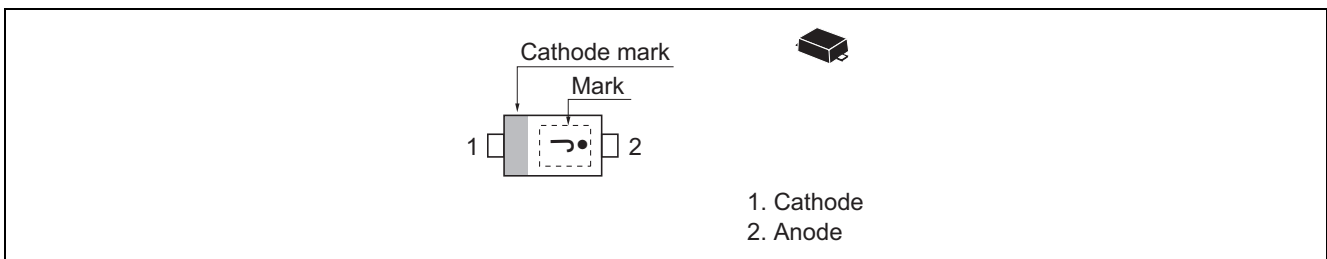
### Features

- An optimal solution for antenna switching in mobile phones.
- Low capacitance. ( $C = 0.35$  pF max)
- Low forward resistance. ( $r_f = 1.3 \Omega$  max)
- Thin Extremely small Flat Lead Package (TEFP) is suitable for surface mount design.

### Ordering Information

Type No.	Laser Mark	Package Name	Package Code
HVL142AM	J	TEFP	PUSF0002ZA-A

### Pin Arrangement



## Absolute Maximum Ratings

(Ta = 25°C)

Item	Symbol	Value	Unit
Reverse voltage	$V_R$	30	V
Forward current	$I_F$	100	mA
Power dissipation	$P_d$	100	mW
Junction temperature	$T_j$	125	°C
Storage temperature	$T_{stg}$	-55 to +125	°C

## Electrical Characteristics

(Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Condition
Reverse current	$I_R$	—	—	100	nA	$V_R = 30\text{ V}$
Forward voltage	$V_F$	—	—	1.0	V	$I_F = 10\text{ mA}$
Capacitance	C	—	—	0.35	pF	$V_R = 1\text{ V}, f = 1\text{ MHz}$
Forward resistance	$r_f$	—	—	1.3	$\Omega$	$I_F = 10\text{ mA}, f = 100\text{ MHz}$
ESD-Capability *1	—	100	—	—	V	C = 200 pF, R = 0 $\Omega$ , Both forward and reverse direction 1 pulse.

Notes: 1. Failure criterion ;  $I_R > 100\text{ nA}$  at  $V_R = 30\text{ V}$

2. For TAFP package, the material of lead is exposed for cutting plane. There for, soldering nature of lead tip part is considered as unquestioned. Please kindly consider soldering nature.

Main Characteristic

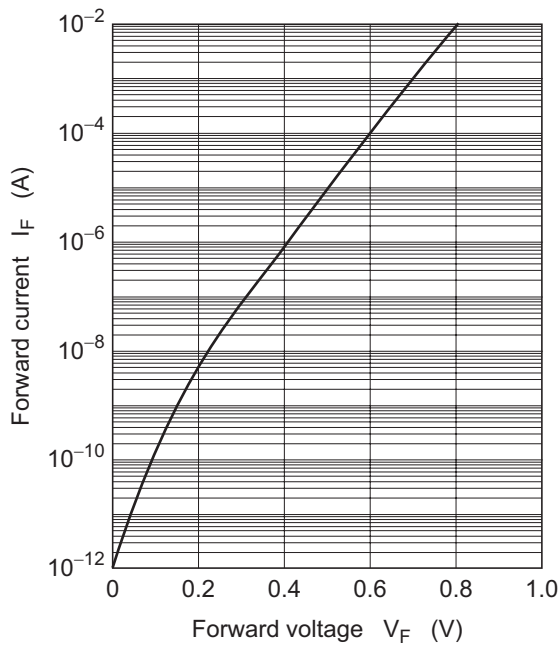


Fig.1 Forward current vs. Forward voltage

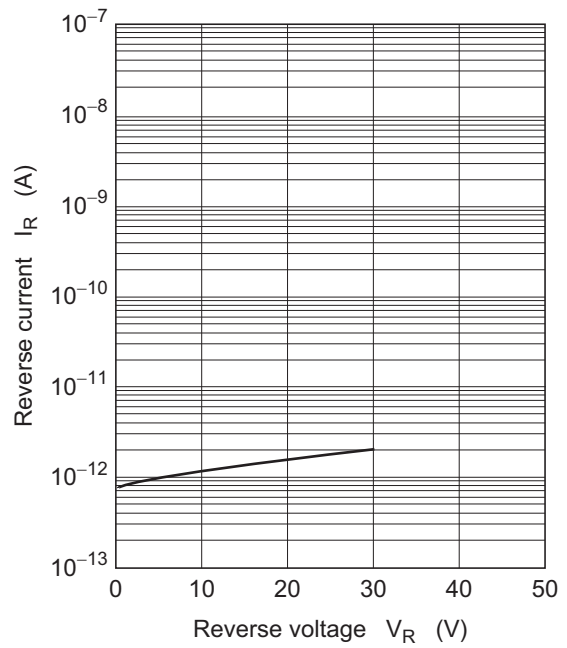


Fig.2 Reverse current vs. Reverse voltage

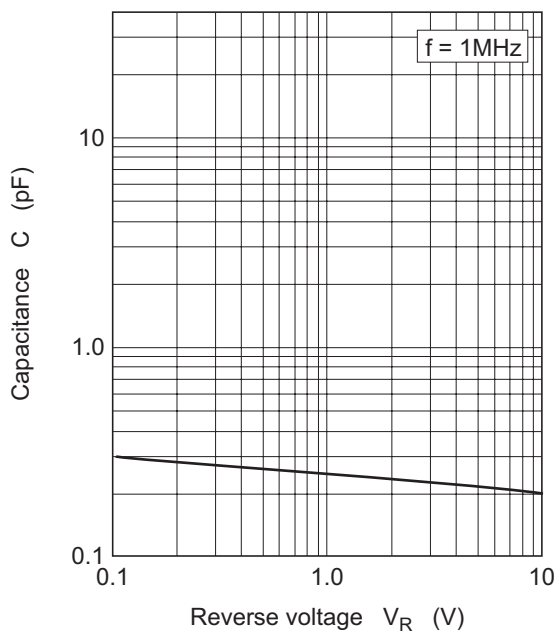


Fig.3 Capacitance vs. Reverse voltage

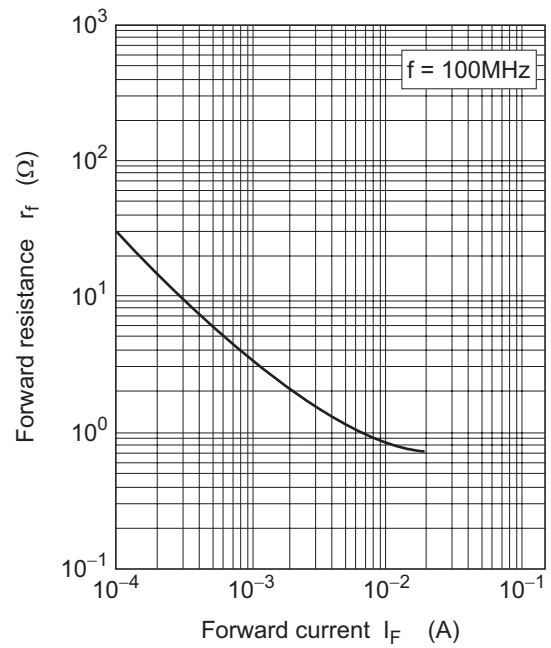


Fig.4 Forward resistance vs. Forward current

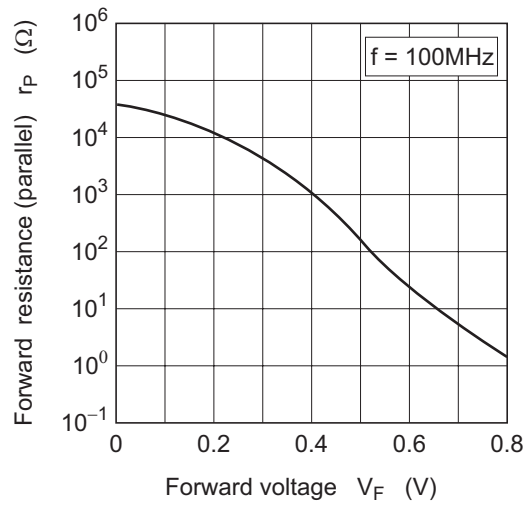
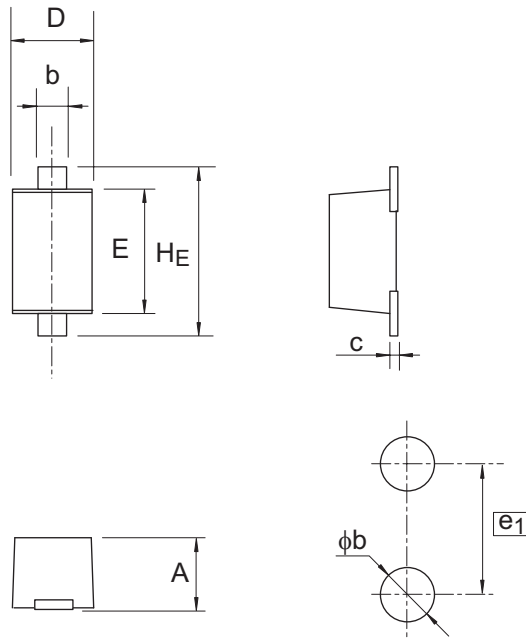


Fig.5 Forward resistance (parallel) vs. Forward voltage

### Package Dimensions

Package Name TEFP	JEITA Package Code —	RENESAS Code PUSF0002ZA-A	Previous Code TEFP / TEFPV	MASS[Typ.] 0.0006g
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Pattern of terminal position areas

Reference Symbol	Dimension in Millimeters		
	Min	Nom	Max
A	-	-	0.40
b	0.25	0.30	0.35
c	0.08	0.13	0.18
D	0.55	0.60	0.65
E	0.75	0.80	0.90
$H_E$	0.95	1.00	1.05
$\phi b$	-	0.40	-
$e_1$	-	1.00	-

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